

NPN RF POWER TRANSISTOR

DESCRIPTION:

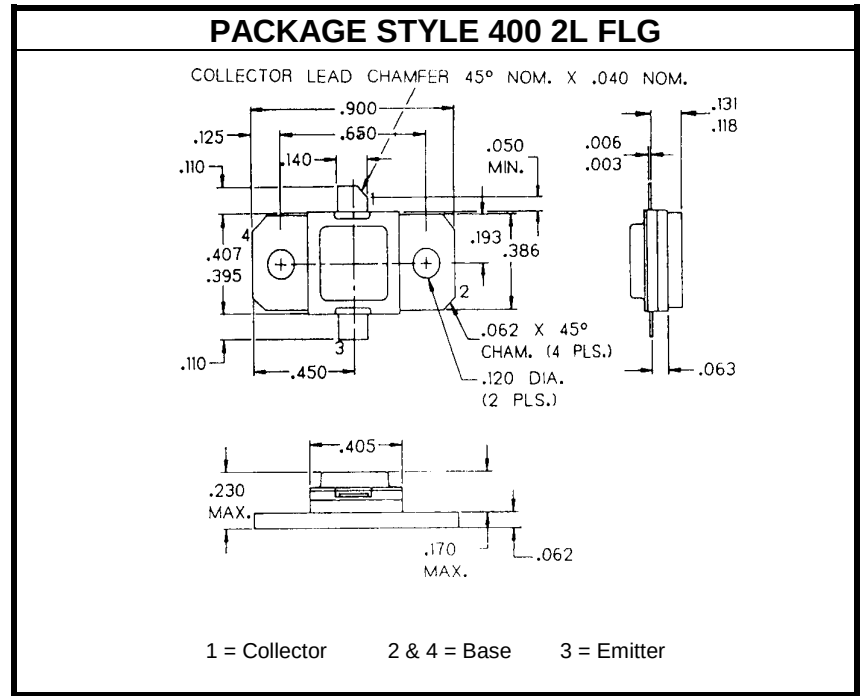
The **ASAT35L** is a Common Base Transistor Designed for L-Band Satcom Amplifier Applications.

FEATURES INCLUDE:

- Input/Output Matching Networks
- Gold Metallization
- Emitter Ballasting

MAXIMUM RATINGS

I_C	3.5 A
V_{CBO}	50 V
P_{DISS}	55 W @ $T_C = 25^\circ\text{C}$
T_J	-55°C to $+200^\circ\text{C}$
T_{STG}	-55°C to $+200^\circ\text{C}$
θ_{JC}	2.6°C/W



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 20\text{ mA}$			50			V
BV_{CES}	$I_C = 20\text{ mA}$			50			V
BV_{EBO}	$I_E = 10\text{ mA}$			3.5			V
I_{CES}	$V_{CE} = 28\text{ V}$					5.0	mA
h_{FE}	$V_{CE} = 5\text{ V}$	$I_C = 2.0\text{ A}$		20		300	---
P_G η_c	$V_{CE} = 28\text{ V}$	$P_{OUT} = 35\text{ W}$	$f = 1500 - 1600\text{ MHz}$	8.0 45	9.0 50		dB %
Z_{CL} Z_{IN}	$V_{CE} = 28\text{ V}$	$P_{OUT} = 35\text{ W}$	$f = 1500\text{ MHz}$	3.0 + j0.5 4.0 + j15.0			Ohms
Z_{CL} Z_{IN}	$V_{CE} = 28\text{ V}$	$P_{OUT} = 35\text{ W}$	$f = 1600\text{ MHz}$	1.8 + j1.0 5.5 + j16.2			Ohms